

30 V, 154 mA, Single, N-Channel, Gate ESD Protection, SC-89

2N7002NT1

Features

- Low Gate Charge for Fast Switching
- Small 1.6 X 1.6 mm Footprint
- ESD Protected Gate
- **Pb-Free package is available**
RoHS product for packing code suffix "G"
Halogen free product for packing code suffix "H"

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

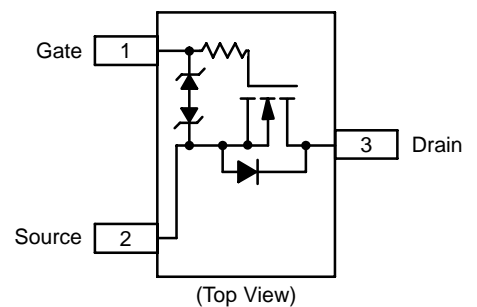
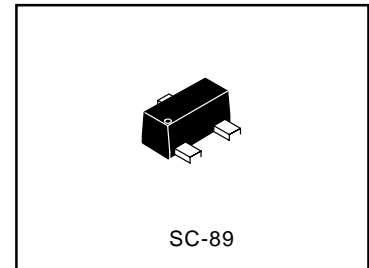
Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V _{DSS}	30	V
Gate-to-Source Voltage		V _{GS}	± 10	V
Continuous Drain Current (Note 1)	Steady State = 25°C	I _D	154	mA
Power Dissipation (Note 1)	Steady State = 25°C	P _D	300	mW
Pulsed Drain Current	t _p ≤ 10 μs	I _{DM}	618	mA
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 150	°C
Continuous Source Current (Body Diode)		I _{SD}	154	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C

THERMAL RESISTANCE RATINGS

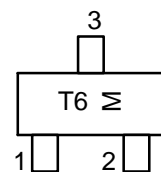
Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	R _{θJA}	416	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



MARKING DIAGRAM



TF = Specific Device Code
M = Month Code

ORDERING INFORMATION

Device	Marking	Shipping
2N7002NT1	T6	3000/Tape&Reel

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}$			1.0	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V},$ $T = 85^\circ\text{C}$			1.0	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 25	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 1.0	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V},$ $T = 85^\circ\text{C}$			± 1.0	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 154\text{ mA}$		1.4	7.0	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 154\text{ mA}$		2.3	7.5	
Forward Transconductance	g_{FS}	$V_{DS} = 3\text{ V}, I_D = 154\text{ mA}$		80		mS

CAPACITANCES

Input Capacitance	C_{ISS}	$V_{DS} = 5.0\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0\text{ V}$		11.5		pF
Output Capacitance	C_{OSS}			10		
Reverse Transfer Capacitance	C_{RSS}			3.5		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 5.0\text{ V},$ $I_D = 75\text{ mA}, R_G = 10\text{ }\Omega$		13		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			98		
Fall Time	t_f			60		

Drain-Source Diode Characteristics

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 0.154\text{ mA}$		0.77	0.9	V
-----------------------	----------	--	--	------	-----	---

2. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.



TYPICAL PERFORMANCE CURVES

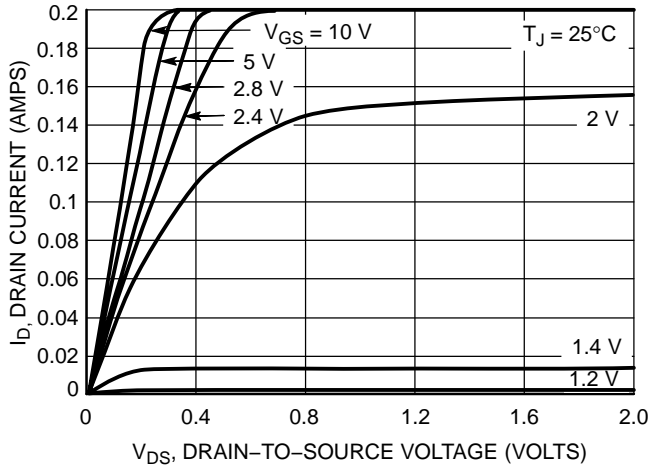


Figure 1. On-Region Characteristics

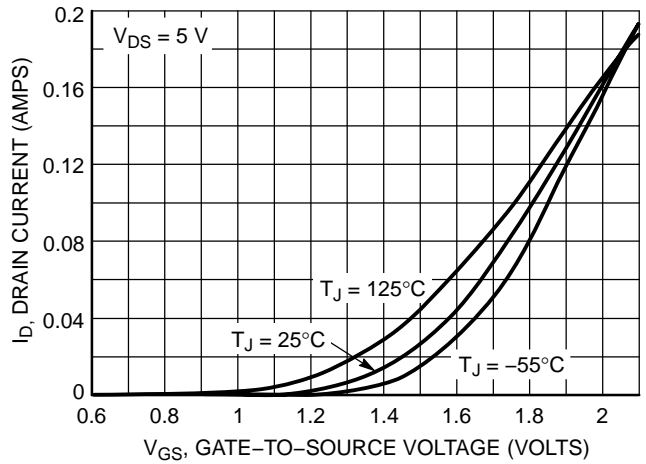


Figure 2. Transfer Characteristics

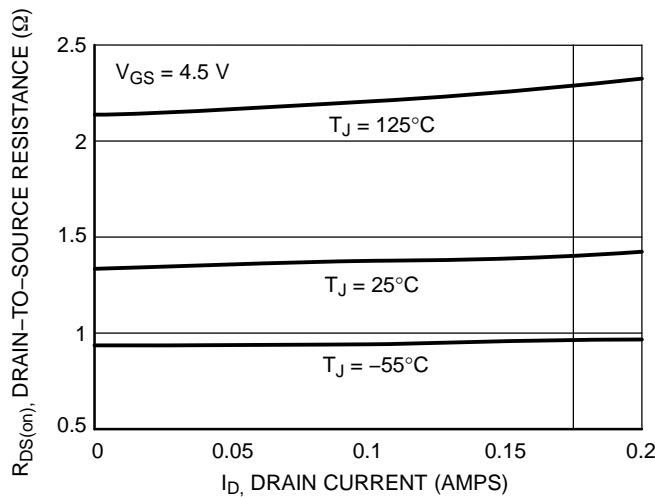


Figure 3. On-Resistance vs. Drain Current and Temperature

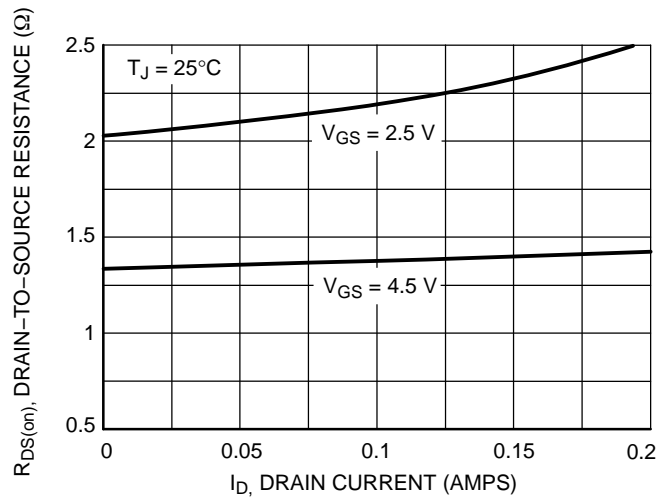


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

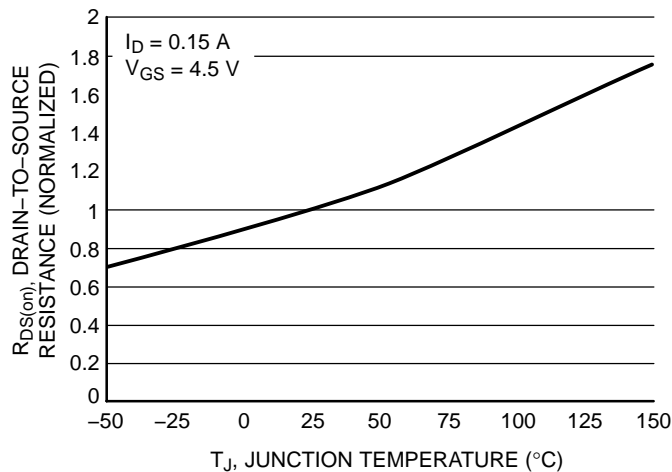


Figure 5. On-Resistance Variation with Temperature

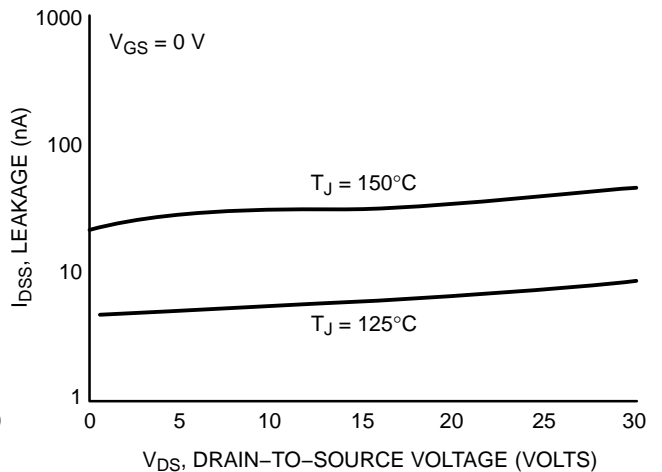


Figure 6. Drain-to-Source Leakage Current vs. Voltage



TYPICAL PERFORMANCE CURVES

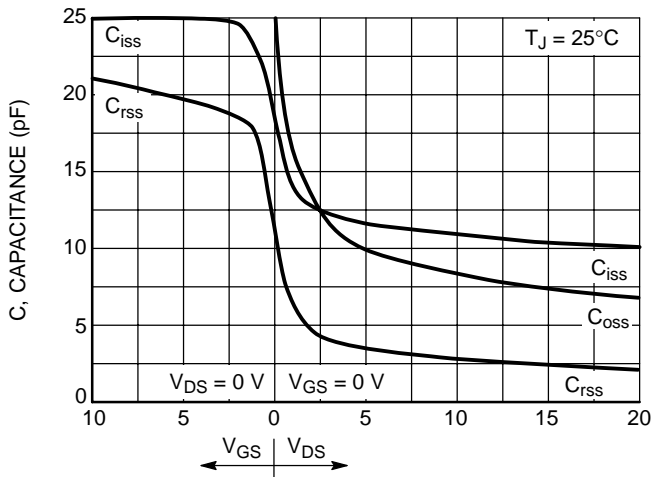


Figure 7. Capacitance Variation

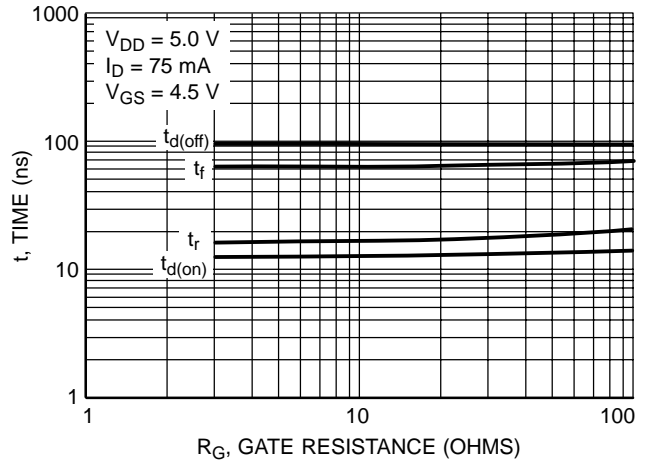


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

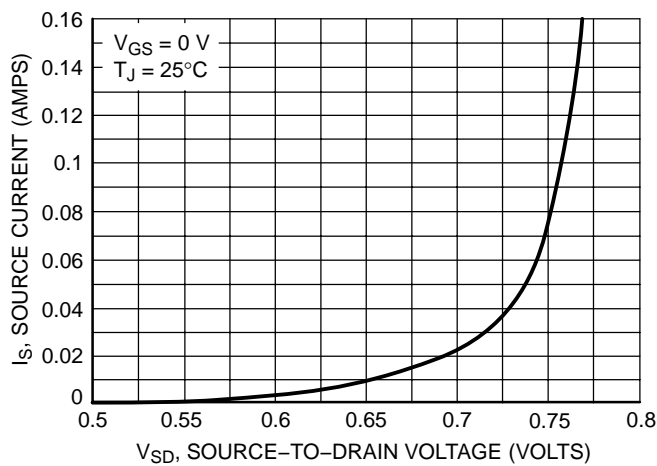
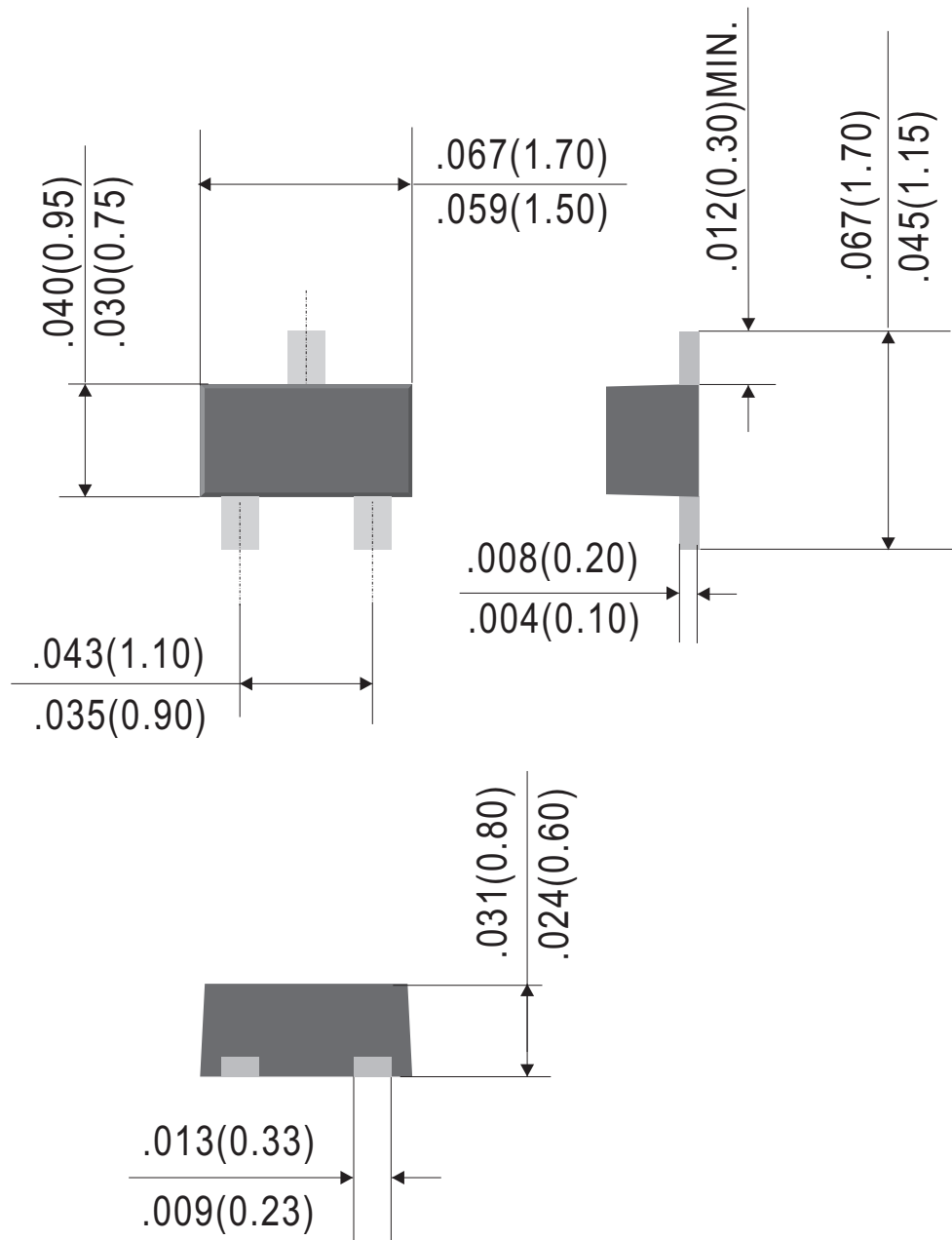


Figure 9. Diode Forward Voltage vs. Current



SC-89



Dimensions in inches and (millimeters)

Ordering Information:

Device PN	Packing
2N7002NT1G ⁽¹⁾ -WS	Tape&Reel: 3 Kpcs/Reel

Note: (1) RoHS product for packing code suffix "G" ; Halogen free product for packing code suffix "H"

*****Disclaimer*****

WILLAS reserves the right to make changes without notice to any product specification herein, to make corrections, modifications, enhancements or other changes. WILLAS or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies. Data sheet specifications and its information contained are intended to provide a product description only. "Typical" parameters which may be included on WILLAS data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. WILLAS does not assume any liability arising out of the application or use of any product or circuit.

WILLAS products are not designed, intended or authorized for use in medical, life-saving implant or other applications intended for life-sustaining or other related applications where a failure or malfunction of component or circuitry may directly or indirectly cause injury or threaten a life without expressed written approval of WILLAS. Customers using or selling WILLAS components for use in such applications do so at their own risk and shall agree to fully indemnify WILLAS Inc and its subsidiaries harmless against all claims, damages and expenditures.